

# RJK03C0DPA

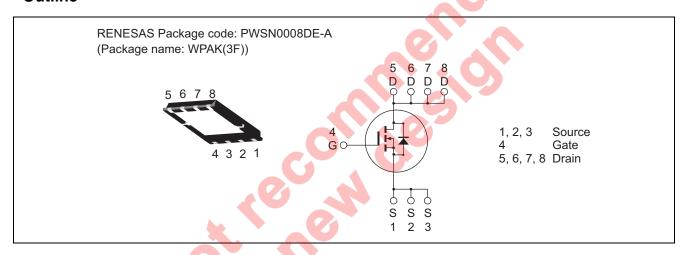
30V, 70A,  $2.0m\Omega$  max. N Channel Power MOS FET High Speed Power Switching

R07DS0921EJ0400 Rev.4.00 Mar 22, 2013

#### **Features**

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free
- Halogen-free

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	70	A
Drain peak current	I <sub>D(pulse)</sub> Note1	280	A
Body-drain diode reverse drain current	I <sub>DR</sub>	70	A
Avalanche current	I <sub>AP</sub> Note 2	35	A
Avalanche energy	E <sub>AR</sub> Note 2	122	mJ
Channel dissipation	Pch Note3	65	W
Channel to case thermal impedance	θch-c Note3	1.93	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3.  $Tc = 25^{\circ}C$

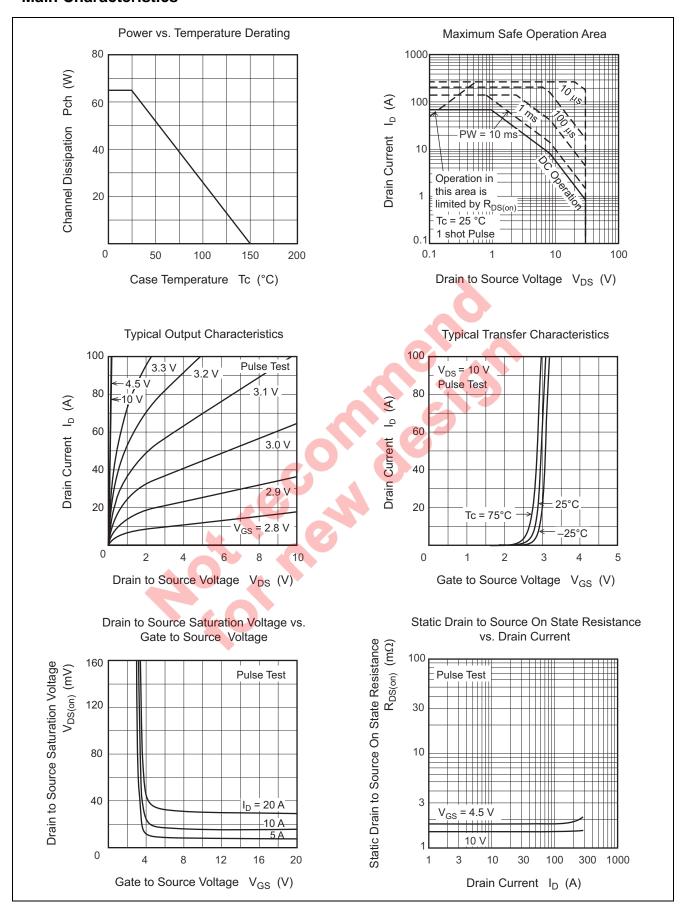
#### **Electrical Characteristics**

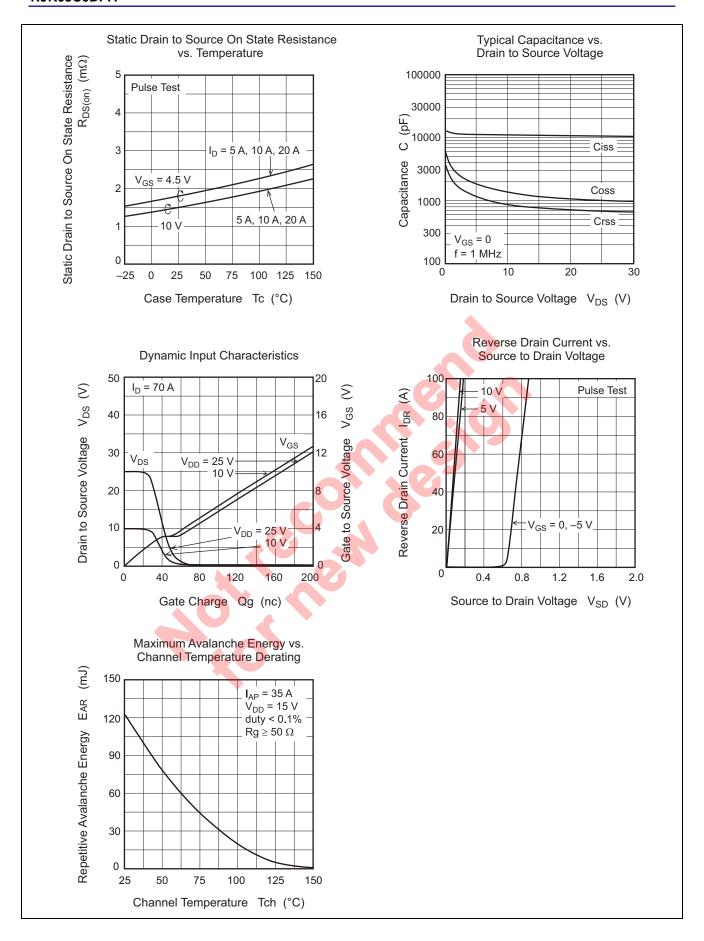
 $(Ta = 25^{\circ}C)$ 

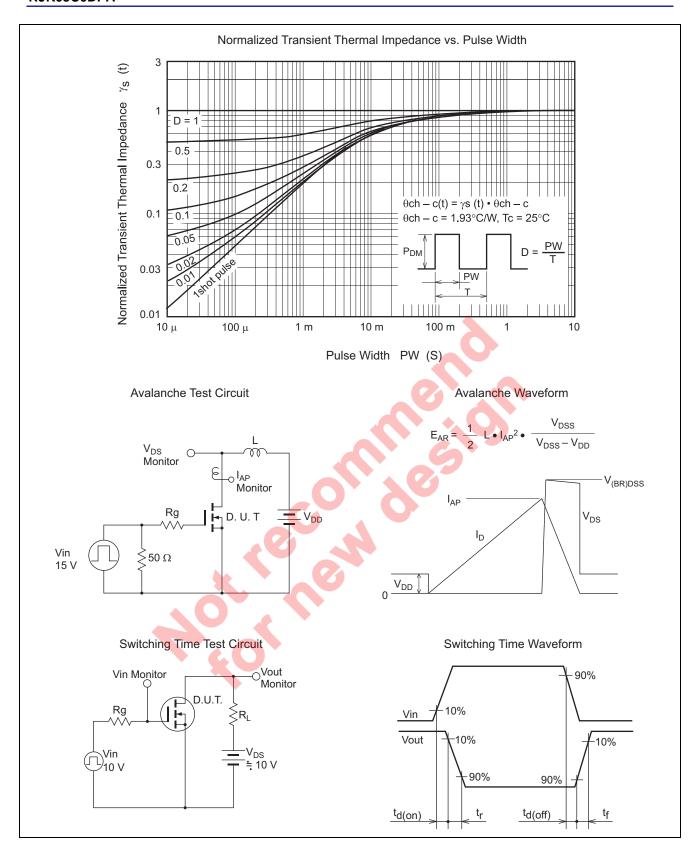
Drain to source breakdown voltage   V <sub>(BRIDSS</sub>   30   —   —   V   I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0	Item	Symbol	Min	Тур	Max	Unit	Test Conditions
	Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	30	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
	Gate to source leak current	I <sub>GSS</sub>	_	_	± 0.5	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.2	_	2.5	V	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Static drain to source on state	R <sub>DS(on)</sub>		1.5	2.0	mΩ	$I_D = 35 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
$ \begin{array}{ l c c c c c c c c c c c c c c c c c c $	resistance	R <sub>DS(on)</sub>		1.8	2.5	mΩ	$I_D = 35 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Forward transfer admittance	y <sub>fs</sub>	_	210	_	S	$I_D = 35 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Reverse transfer capacitance $Crss$ $ 870$ $ pF$ $f$ $=$ 1 MHz $Gate Resistance Rg  0.75  \Omega Gate Resistance Rg  0.75  \Omega Gate to source charge Qg  66  nC V_{DD} = 10 V V_{GS} = 4.5 V V_{GS} = 10 V_$	Input capacitance	Ciss	_	11000	_	pF	V <sub>DS</sub> = 10 V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output capacitance	Coss	_	1440	_	pF	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse transfer capacitance	Crss		870	_	pF	f = 1 MHz
Gate to source charge $Qgs$ — $42$ — $nC$ $V_{GS} = 4.5 V$ $I_{D} = 70 A$ $I_{D} = 35 A$ $I_{D} = 10 V$ $I_{D} = 35 A$ $I_{D} = 10 V$ $I_{D}$	Gate Resistance	Rg	_	0.75	_	Ω	
Gate to drain charge $\begin{array}{cccccccccccccccccccccccccccccccccccc$	Total gate charge	Qg	_	66	_	nC	V <sub>DD</sub> = 10 V
Turn-on delay time $\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate to source charge	Qgs	_	42	_	nC	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate to drain charge	Qgd	_	13.7	_	nC	$I_D = 70 \text{ A}$
Turn-off delay time $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-on delay time	t <sub>d(on)</sub>	_	28	_	ns	$V_{GS} = 10 \text{ V}, I_D = 35 \text{ A}$
Fall time $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Rise time	t <sub>r</sub>	_	14.2	-(0	ns	
Body-drain diode forward voltage $V_{DF}$ — 0.80 1.04 $V_{F}$ Is = 70 A, $V_{GS} = 0$ Note4  Body-drain diode reverse recovery $t_{rr}$ — 53 — ns $I_{F} = 70$ A, $V_{GS} = 0$	Turn-off delay time	t <sub>d(off)</sub>	_	102		ns	
Body-drain diode reverse recovery $t_{rr}$ — 53 — ns $I_F = 70 \text{ A}, V_{GS} = 0$	Fall time	t <sub>f</sub>	_	40		ns	) -
time $\frac{di_{-}}{dt} = 100 \text{ A/us}$	Body-drain diode forward voltage	$V_{DF}$	_	0.80	1.04	V	$I_F = 70 \text{ A}, V_{GS} = 0^{\text{Note4}}$
time  Notes: 4. Pulse test	Body-drain diode reverse recovery	t <sub>rr</sub>		53		ns	,
Notes: 4. Pulse test	time		_			•	di <sub>F</sub> / dt = 100 A/ μs

Notes: 4. Pulse test

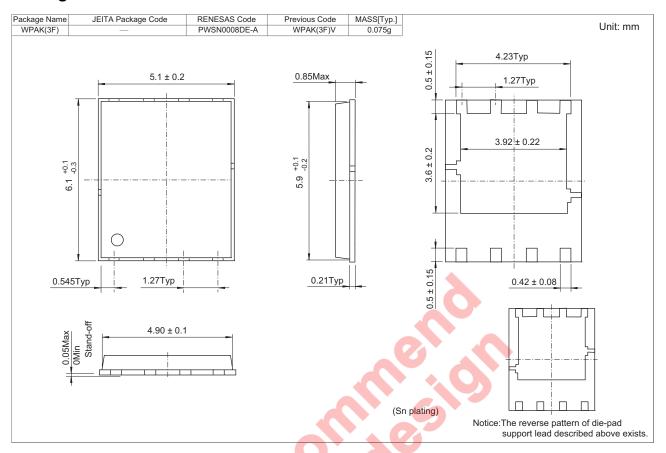
#### **Main Characteristics**







### **Package Dimensions**



## **Ordering Information**

Orderable Part Number	Q	uantity	Shipping Container
RJK03C0DPA-00-J5A	3000 pcs		Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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